

an electrostatic protection element connected in parallel with said MOS capacitor between said ground terminal and said MOS capacitor;

wherein, a wire resistance of said ground potential wire between a connection point on said ground wire with one end of said electrostatic protection element and said ground terminal is larger than a wire resistance of said ground potential wire between said connection point on said ground potential wire with one end of said electrostatic protection element and a connection point on said ground potential wire with the other end of said MOS capacitor.

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2. (Amended) A semiconductor integrated circuit device comprising:

an electrostatic protection element, one end of which is connected to a power source wire for supplying a power source voltage, and another end of which is connected to a ground potential wire for supplying a ground potential;

a ground terminal, to which said ground potential wire is connected; and

a MOS capacitor connected in parallel with said electrostatic protection element between said ground terminal and said electrostatic protection element;

wherein, a wire resistance of said ground potential wire between a connection point on said ground wire with one end of said MOS capacitor and said ground terminal is larger than a wire resistance of the ground potential wire between said connection point on said ground potential wire with one end of said MOS capacitor and a connection point on said ground potential wire with the other end of said electrostatic protection element.

5. (*Amended*) A semiconductor integrated circuit device comprising:

an input/output terminal;

a first electrostatic protection element, one end of which is connected to said input/output terminal and another end of which is connected to a ground potential wire for supplying the ground potential;

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a second electrostatic protection element, one end of which is connected to a power source wire for supplying a power source voltage, and another end of which is connected to a ground potential wire for supplying the ground potential; and

a MOS capacitor connected in parallel with said second electrostatic protection element between said first electrostatic protection element and said second electrostatic protection element;

wherein a wire resistance of the ground potential wire between the connection point on the ground potential wire with the other end of said first electrostatic protection element and the connection point on the ground potential wire with one end of said MOS capacitor is larger than a wire resistance of the ground potential wire between the connection point on the ground potential wire with the one end of said MOS capacitor and the connection point on the ground potential wire with the other end of said second electrostatic protection element.

12. (*Amended*) A semiconductor integrated circuit device according to any one of claims

1 and 2, wherein said electrostatic protection element is a MOS field effect transistor, the drain

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of which is connected to said power source wire, and the source and the gate of which are connected to said ground potential wire.

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13. (*Amended*) A semiconductor integrated circuit device according to any one of claims 4 and 5, wherein said second electrostatic protection element is a MOS field effect transistor, the drain of which is connected to said power source wire, and the source and the gate of which are connected to said ground potential wire.
